

AMENDMENT TO THE SPECIFICATION:**IN THE ABSTRACT**

Please amend the Abstract of the invention as follows:

~~The invention provides methods~~ A method for determining film continuity and growth modes in thin dielectric films. ~~The continuity determining method comprises:~~ includes: depositing a material on the substrate using a first value of a growth metric; depositing an amount of charge on a surface of the material; repetitively measuring a surface voltage of the material until an onset of tunneling to provide a V_{tunnel} (or E_{tunnel}) value; repeating the above steps for different values of the growth metric; and comparing the V_{tunnel} (or E_{tunnel}) values for different values of the growth metric to provide a measure of the continuity of the material on the substrate. The growth modes of the material can be determined by comparing the first derivative of the V_{tunnel} (or E_{tunnel}) per growth metric curve versus the growth metric, and examining the linearity of the results of the comparison. The growth metric parameters may include thickness, time, precursor cycles, or temperature.